## PROCEEDINGS OF SPIE

# Advanced Etch Technology for Nanopatterning IX

**Richard S. Wise Catherine B. Labelle** *Editors* 

25–26 February 2020 San Jose, California, United States

Sponsored and Published by SPIE

Volume 11329

Proceedings of SPIE 0277-786X, V. 11329

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Advanced Etch Technology for Nanopatterning IX, edited by Richard S. Wise, Catherine B. Labelle, Proc. of SPIE Vol. 11329, 1132901 · © 2020 SPIE · CCC code: 0277-786X/20/\$21 · doi: 10.1117/12.2571137

Proc. of SPIE Vol. 11329 1132901-1

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Author(s), "Title of Paper," in Advanced Etch Technology for Nanopatterning IX, edited by Richard S. Wise, Catherine B. Labelle, Proceedings of SPIE Vol. 11329 (SPIE, Bellingham, WA, 2020) Seven-digit Article CID Number.

ISSN: 0277-786X ISSN: 1996-756X (electronic)

ISBN: 9781510634251 ISBN: 9781510634268 (electronic)

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